

SiT2018B

High Temp, Single-Chip, One-Output Clock Generator


Table 1. Electrical Characteristics (continued)

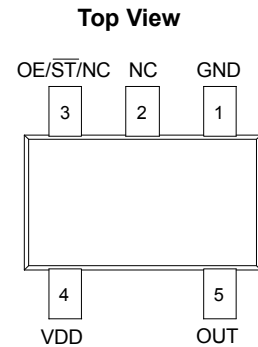
Parameters	Symbol	Min.	Typ.	Max.	Unit	Condition
Input Characteristics						
Input High Voltage	V _{IH}	70%	–	–	V _{dd}	Pin 3, OE or \overline{ST}
Input Low Voltage	V _{IL}	–	–	30%	V _{dd}	Pin 3, OE or \overline{ST}
Input Pull-up Impedance	Z _{in}	50	87	150	k Ω	Pin 3, OE logic high or logic low, or \overline{ST} logic high
		2	–	–	M Ω	Pin 3, \overline{ST} logic low
Startup and Resume Timing						
Startup Time	T _{start}	–	–	5	ms	Measured from the time V _{dd} reaches its rated minimum value
Enable/Disable Time	T _{oe}	–	–	130	ns	f = 110 MHz. For other frequencies, T _{oe} = 100 ns + 3 * clock periods
Resume Time	T _{resume}	–	–	5	ms	Measured from the time ST pin crosses 50% threshold
Jitter						
RMS Period Jitter	T _{jitt}	–	1.6	2.5	ps	f = 75 MHz, V _{dd} = 2.5V, 2.8V, 3.0V or 3.3V
		–	1.9	3	ps	f = 75 MHz, V _{dd} = 1.8V
Peak-to-peak Period Jitter	T _{pk}	–	12	20	ps	f = 75 MHz, V _{dd} = 2.5V, 2.8V, 3.0V or 3.3V
		–	14	25	ps	f = 75 MHz, V _{dd} = 1.8V
RMS Phase Jitter (random)	T _{phj}	–	0.5	0.8	ps	f = 75 MHz, Integration bandwidth = 900 kHz to 7.5 MHz
		–	1.3	2	ps	f = 75 MHz, Integration bandwidth = 12 kHz to 20 MHz

Table 2. Pin Description

Pin	Symbol		Functionality
1	GND	Power	Electrical ground
2	NC	No Connect	No connect
3	OE/ \overline{ST} /NC	Output Enable	H ^[1] : specified frequency output L: output is high impedance. Only output driver is disabled.
		Standby	H or Open ^[1] : specified frequency output L: output is low (weak pull down). Device goes to sleep mode. Supply current reduces to I _{std} .
		No Connect	Any voltage between 0 and V _{dd} or Open ^[1] : Specified frequency output. Pin 3 has no function.
4	VDD	Power	Power supply voltage ^[2]
5	OUT	Output	Oscillator output

Notes:

- In OE or \overline{ST} mode, a pull-up resistor of 10 k Ω or less is recommended if pin 3 is not externally driven. If pin 3 needs to be left floating, use the NC option.
- A capacitor of value 0.1 μ F or higher between V_{dd} and GND is required.


Figure 1. Pin Assignments

SiT2018B

High Temp, Single-Chip, One-Output Clock Generator


Table 3. Absolute Maximum Limits

Attempted operation outside the absolute maximum ratings of the part may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	150	°C
Vdd	-0.5	4	V
Electrostatic Discharge	–	2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	–	260	°C
Junction Temperature ^[3]	–	150	°C

Note:

3. Exceeding this temperature for extended period of time may damage the device.

Table 4. Thermal Consideration^[4]

Package	θ_{JA} , 4 Layer Board (°C/W)	θ_{JC} , Bottom (°C/W)
SOT23-5	421	175

Note:

4. Refer to JESD51 for θ_{JA} and θ_{JC} definitions, and reference layout used to determine the θ_{JA} and θ_{JC} values in the above table.

Table 5. Maximum Operating Junction Temperature^[5]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
105°C	115°C
125°C	135°C

Note:

5. Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

Table 6. Environmental Compliance

Parameter	Condition/Test Method
Mechanical Shock	MIL-STD-883F, Method 2002
Mechanical Vibration	MIL-STD-883F, Method 2007
Temperature Cycle	JESD22, Method A104
Solderability	MIL-STD-883F, Method 2003
Moisture Sensitivity Level	MSL1 @ 260°C

SiT2018B

High Temp, Single-Chip, One-Output Clock Generator



Test Circuit and Waveform^[6]

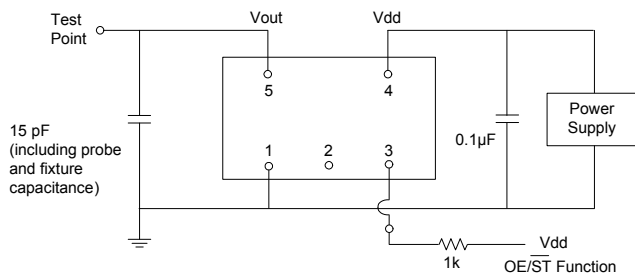


Figure 2. Test Circuit

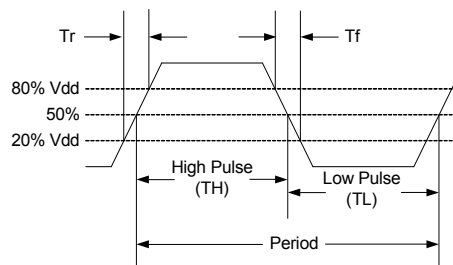
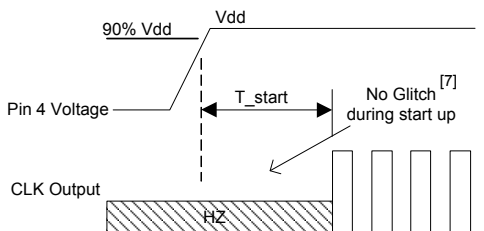


Figure 3. Output Waveform

Note:

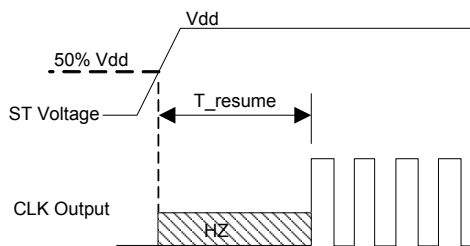
6. Duty Cycle is computed as $Duty\ Cycle = TH/Period$.

Timing Diagrams



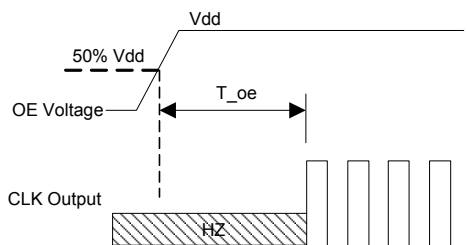
T_{start} : Time to start from power-off

Figure 4. Startup Timing (OE/ST Mode)



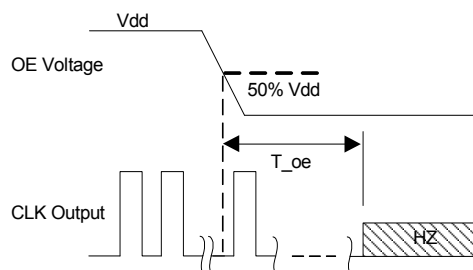
T_{resume} : Time to resume from ST

Figure 5. Standby Resume Timing (ST Mode Only)



T_{oe} : Time to re-enable the clock output

Figure 6. OE Enable Timing (OE Mode Only)



T_{oe} : Time to put the output in High Z mode

Figure 7. OE Disable Timing (OE Mode Only)

Note:

7. SiT2018 has “no runt” pulses and “no glitch” output during startup or resume.

SiT2018B

High Temp, Single-Chip, One-Output Clock Generator



The Smart Timing Choice™

Performance Plots^[8]

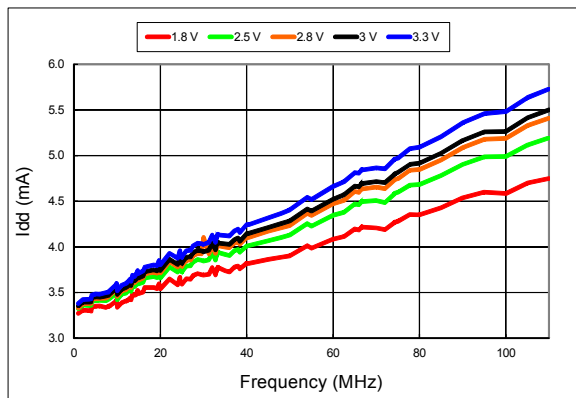


Figure 8. Idd vs Frequency

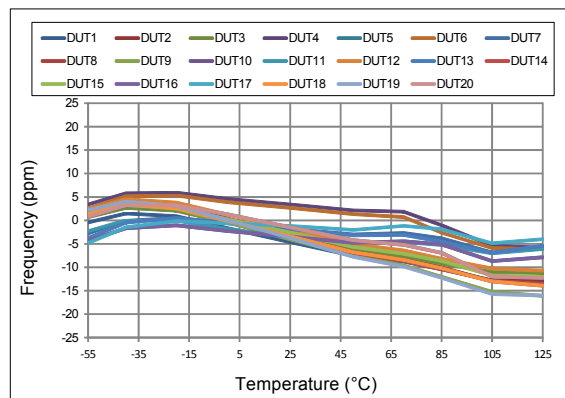


Figure 9. Frequency vs Temperature

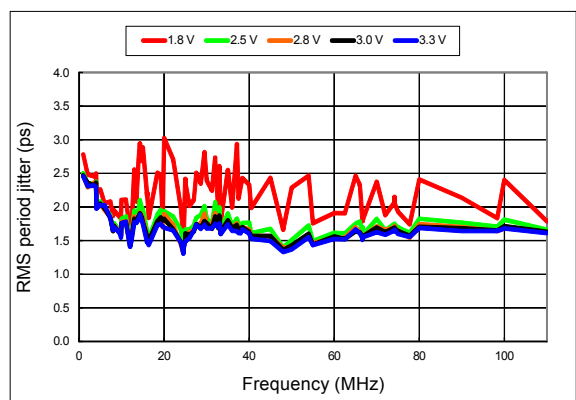


Figure 10. RMS Period Jitter vs Frequency

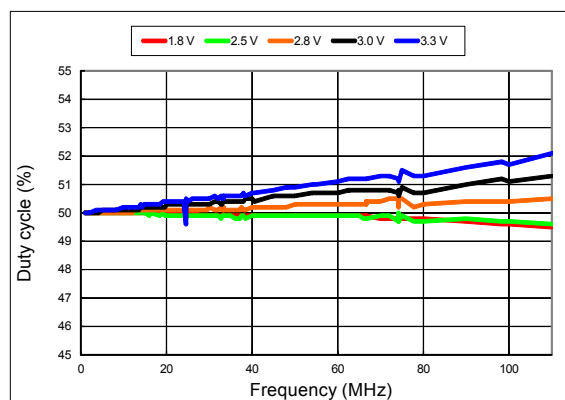


Figure 11. Duty Cycle vs Frequency

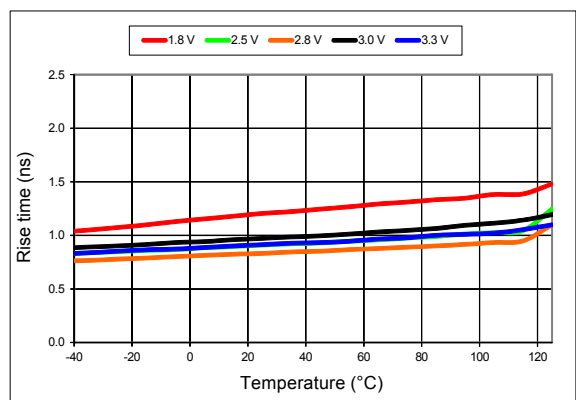


Figure 12. 20%-80% Rise Time vs Temperature

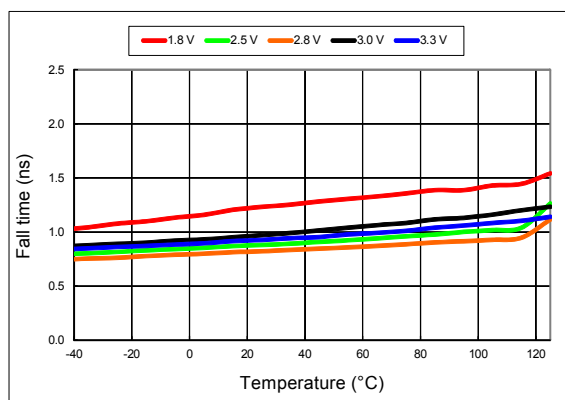


Figure 13. 20%-80% Fall Time vs Temperature

SiT2018B

High Temp, Single-Chip, One-Output Clock Generator



The Smart Timing Choice™

Performance Plots^[8]

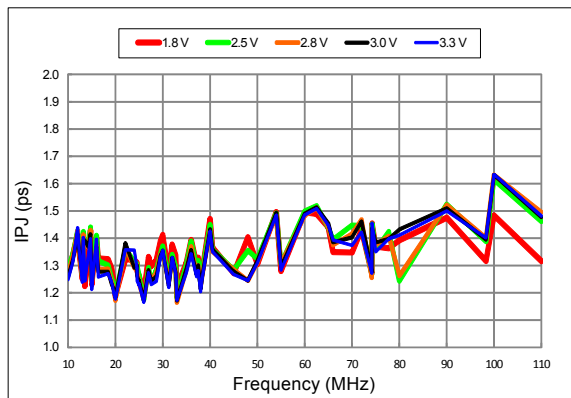


Figure 14. RMS Integrated Phase Jitter Random (12k to 20 MHz) vs Frequency^[9]

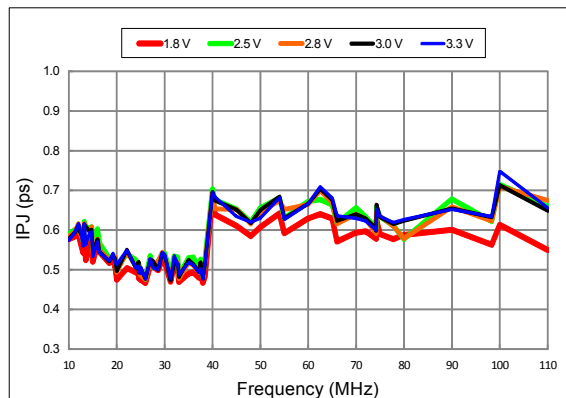


Figure 15. RMS Integrated Phase Jitter Random (900 kHz to 20 MHz) vs Frequency^[9]

Notes:

- 8. All plots are measured with 15 pF load at room temperature, unless otherwise stated.
- 9. Phase noise plots are measured with Agilent E5052B signal source analyzer. Integration range is up to 5 MHz for carrier frequencies up to 40 MHz.

